

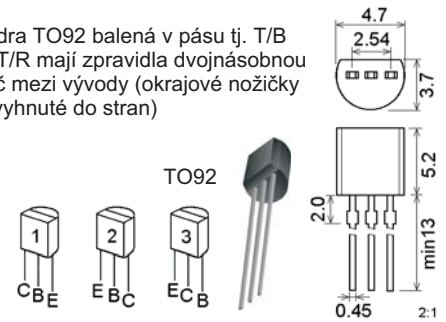
# TRANZISTORY BIPOLÁRNÍ

## Tranzistory NF do 1.5W

objednáací název		Uce	Ic	P	B	f	Uces	pouzdro
NPN	PNP	V	A	W		MHz	V	
BC547B	BC557B	45	0.1	0.5	200~450	100	0.6	TO92 (1)
BC547C	BC557C T/B	45	0.1	0.5	420~800	100	0.6	TO92 (1)
BC546B	BC556B	65	0.1	0.5	200~450	100	0.6	TO92 (1)
2N3904 T/B	2N3906 T/B	40	0.2	0.6	> 30	250	0.3~0.4	TO92 (2)
MPSA42 T/R	MPSA92 T/R	300	0.5	0.6	> 25	50	0.5	TO92 (2)
	2N5401	150	0.6	0.6	> 50	100	0.5	TO92 (2)
BC337-25 T/B	BC327-25	45	0.8	0.6	160~400	100	0.7	TO92 (1)
BC337-40	BC327-40	45	0.8	0.6	250~600	100	0.7	TO92 (1)
BC639	BC640 T/B	80	1.0	0.8	40~160	100	0.5	TO92 (3)

novinka!

Pouzdra TO92 balená v pásu tj. T/B příp. T/R mají zpravidla dvojnásobnou rozteč mezi vývody (okrajové nožičky jsou vyhnuté do stran)

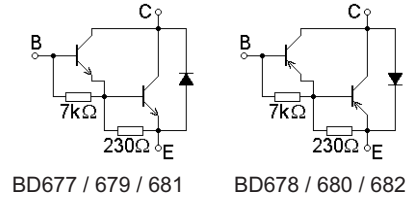
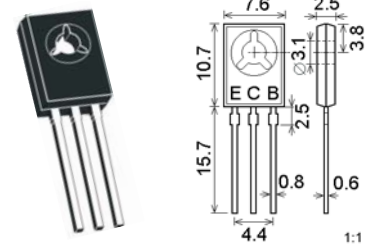


## Tranzistory NF 1.5W a více

objednáací název		Uce	Ic	P	B	f	Uces	pouzdro
NPN	PNP	V	A	W		MHz	V	
BD135-16	BD136-16	45	1.5	8	100~250	50	0.5	TO126
BD137-16	BD138-16	60	1.5	8	100~250	50	0.5	TO126
BD139-10	BD140-10	80	1.5	8	60~160	50	0.5	TO126
BD139-16	BD140-16	80	1.5	8	100~250	50	0.5	TO126
BD139	BD140	80	1.5	8	25~250	50	0.5	TO126
BD237	BD238	80	2	25	40~250	3	0.6	TO126
BD437		45	4	36	> 30	3	0.6	TO126
BD439		60	4	36	> 20	3	0.8	TO126
BD441	BD442	80	4	36	40~140	3	0.8	TO126
BD243C	BD244C	100	6	65	> 15	3	1.5	TO220
MJE15032	MJE15033	250	8	50	> 10	30	0.5	TO220
BD711	BD712	100	12	75	> 15	3	1.0	TO220
BD911	BD912	100	15	90	> 5	3	3.0	TO220
TIP3055	TIP2955	60	15	90	> 5		3.0	TO247

novinka!

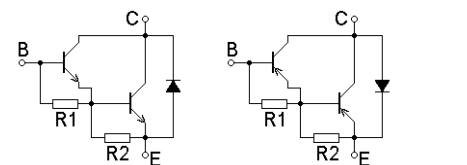
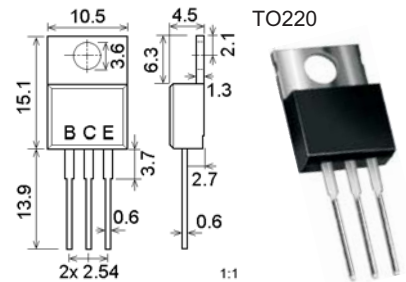
TO126 (SOT32)



## Tranzistory Darlington

objednáací název		Uce	Ic	P	B	f	Uces	pouzdro
NPN	PNP	V	A	W		MHz	V	
BC517		30	1	0.6	> 30 000	200	1.0	TO92 (1)
BD679	BD680	80	4	40	> 750	10	2.5	TO126
BD679A	BD680A	80	4	40	> 750	10	2.8	TO126
BD681	BD682	100	4	40	> 750	10	2.5	TO126
TIP122	TIP127	100	5	65	> 1000	10	4.0	TO220
BDX33C	BDX34C	100	10	70	> 750	20	2.5	TO220
BDW93C	BDW94C	100	12	40	> 750	20	3.0	TO220

BD677 / 679 / 681 BD678 / 680 / 682



## Tranzistory výkonový s anti-paralelní diodou

objednáací název		Uce	Ic	P	B	f	Uces	pouzdro
NPN	PNP	V	A	W		MHz	V	
BUL38D		450	5	80	10~60		1.1	TO220

novinka!

## Tranzistory VF > 1GHz

objednáací název		Uce	Ic	P	G	f	pouzdro
NPN	PNP	V	mA	W	dB	GHz	
BFR91A		12	50	0.3	14	5	TO50
BFR96TS		15	100	0.7	11.5	5	TO50

BDW93 / BDX33 / BDX53 BDW94 / BDX34 / BDX54  
TIP110 / 120 / 122 TIP115 / 125 / 127

## Bipolární Tranzistory - parametry

Uce (V) - nejvyšší dovolené napětí kolektor - emitor

Uces(V) - saturační napětí kolektor-emitor

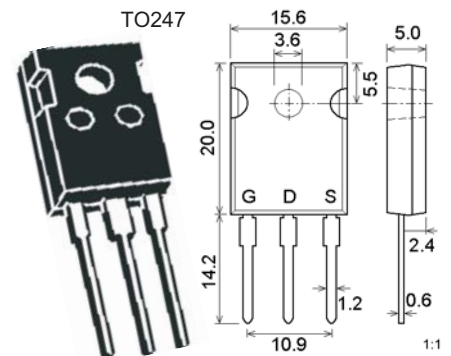
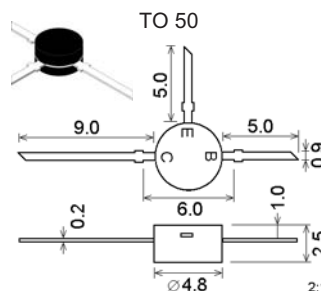
Ic (A) - nejvyšší dovolený proud kolektoru

P (W) - nejvyšší dovolená výkonová ztráta

B - stejnosměrný zesilovací činitel

G (dB) - zisk

f (MHz) - nejvyšší pracovní kmitočet



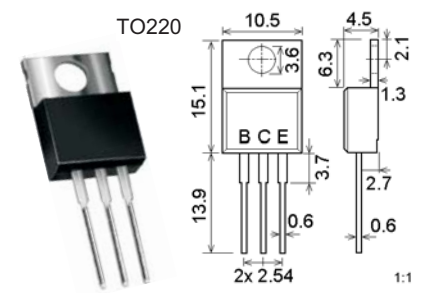
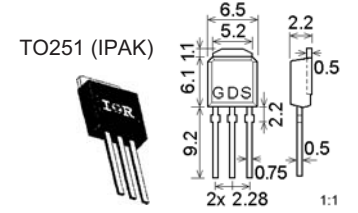
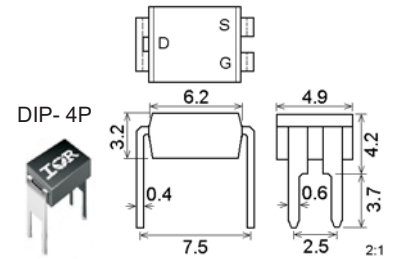
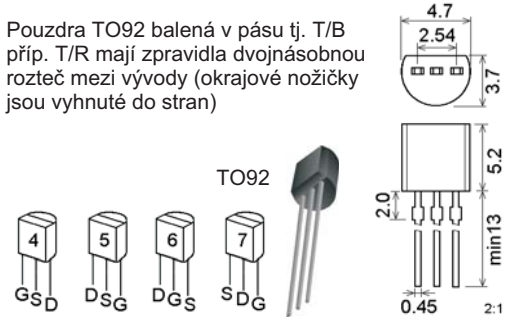
## Tranzistory MOSFET do 1.5W

objednáací název	kanál	U <sub>ds</sub>	I <sub>d</sub>	P	R <sub>ds</sub>	t on/off	pouzdro
kanál N	V	A	W	mΩ	ns		
■ BS108 T/B	N	200	0.25	0.35	8000	15 / 15	TO92 (6)
■ BS170	N	60	0.50	0.83	5000	10 / 10	TO92 (6)
■ IRFD9120	P	100	1.0	1.3	600	40 / 50	DIP-4P

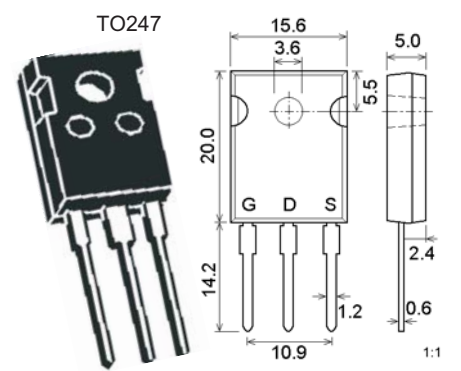
## Tranzistory MOSFET výkonové

objednáací název	kanál	U <sub>ds</sub>	I <sub>d</sub>	P	R <sub>ds</sub>	t on/off	pouzdro
kanál N	V	A	W	mΩ	ns		
■ SPU02N60C3	N	650	1.8	25	3000	10 / 80	TO251
■ IRFU420	N	500	2.4	42	3000	20 / 50	TO251
■ IRLU024N	N	55	17	45	65	80 / 50	TO251
■ STF3NK80Z	N	800	2.5	25	4.5	44 / 76	TO220IS
■ AOTF7T60P	N	700	7	38	1100	72 / 56	TO220IS
■ IRLI530N	N	100	12	41	100	60 / 55	TO220IS
■ IRFI530N	N	100	12	41	110	33 / 62	TO220IS
■ IRFI540N	N	100	20	54	52	50 / 75	TO220IS
■ IRFIZ44N	N	55	31	45	24	76 / 107	TO220IS
■ IRF820	N	500	2.5	50	3000	17 / 49	TO220
■ STP3NK90Z	N	900	3	90	4.8	25 / 63	TO220
■ IRFBG30	N	1000	3.1	125	5000	40 / 120	TO220
■ SPP03N60S5	N	600	3.2	38	1400	60 / 55	TO220
■ STP5NK100Z	N	1000	3.5	125	3700	30 / 70	TO220
■ STP5NK80Z	N	800	4.3	110	2400	45 / 75	TO220
■ IRF830	N	500	4.5	74	1500	24 / 58	TO220
■ IRF840	N	500	8	125	850	40 / 70	TO220
■ IRF520	N	100	9.2	60	270	40 / 40	TO220
■ STP11NK40Z	N	400	10	110	550	40 / 60	TO220
■ IRF740	N	400	10	125	550	40 / 75	TO220
■ STP10NK60Z	N	600	10	35	750	40 / 85	TO220
■ AOT10N60	N	600	10	250	750	74 / 140	TO220
■ IRFZ24N	N	55	17	45	70	40 / 50	TO220
■ IRL640	N	200	17	125	180	90 / 95	TO220
■ IRLZ24N	N	55	18	45	60	80 / 50	TO220
■ IRFB4020	N	200	18	100	100	20 / 22	TO220
■ STP20NF20	N	200	18	110	125	45 / 50	TO220
■ IRF640	N	200	18	125	180	65 / 81	TO220
■ IRFZ34N	N	55	29	68	40	60 / 70	TO220
■ BUZ11	N	50	30	75	40	100 / 300	TO220
■ IRF540N	N	100	33	130	44	45 / 80	TO220
■ IRL540N	N	100	36	140	44	90 / 100	TO220
■ IRLZ44N	N	55	47	110	22	95 / 40	TO220
■ IRFZ44N	N	55	49	94	18	70 / 80	TO220
■ IRF3710	N	100	57	200	23	70 / 100	TO220
■ IRFZ48N	N	55	64	130	14	90 / 85	TO220
■ IRFB4227	N	200	65	330	24	53 / 52	TO220
■ SPP80N06S2L	N	55	80	210	7	55 / 60	TO220
■ STP120N4F6	N	40	80	110	4.3	90 / 60	TO220
■ IRFB4321	N	150	85	350	15	78 / 60	TO220
■ IRFB4410Z	N	100	97	230	9	68 / 100	TO220
■ AOT424	N	30	110	100	4	48 / 73	TO220
■ IRF3205	N	55	110	200	8	115 / 115	TO220
■ IRL3803	N	30	140	200	6	244 / 64	TO220
■ IRF1405	N	55	169	330	5.3	203 / 240	TO220
■ IRFP460LC	N	500	20	280	270	100 / 80	TO247
■ IRFP260N	N	200	50	300	40	80 / 100	TO247
■ IRFP4332	N	250	57	57	29		TO247
■ IRFP054N	N	55	81	170	12	80 / 90	TO247
■ IRFP064N	N	55	110	200	8	115 / 115	TO247
■ IRFP3306	N	60	120	220	4.2	90 / 120	TO247
■ IRFP4568	N	150	171	517	5.9	145 / 130	TO247
■ IRFU9024N	P	55	11	38	175	70 / 60	TO251
■ IRF9520	P	100	6.8	60	600	40 / 46	TO220
■ IRF9520N	P	100	6.8	48	480	60 / 60	TO220
■ IRF9640	P	200	11	125	500	60 / 80	TO220
■ IRF9Z24N	P	55	12	45	175	70 / 60	TO220
■ IRF9530N	P	100	13	75	200	75 / 90	TO220
■ IRF9540	P	100	19	150	200	80 / 80	TO220
■ IRF5210	P	100	40	200	60	103 / 160	TO220
■ IRF4905	P	55	74	200	20	120 / 155	TO220

Pouzdra TO92 balená v pásu tj. T/B příp. T/R mají zpravidla dvojnásobnou rozteč mezi vývody (okrajové nožičky jsou vyhnuté do stran)



TO220IS - chladicí plech oddělen od vnějšího prostředí zalitím v plastovém izolantu (tl. zalitého plechu cca + 1mm)



### FET tranzistory - parametry

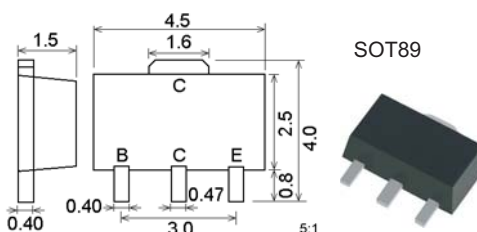
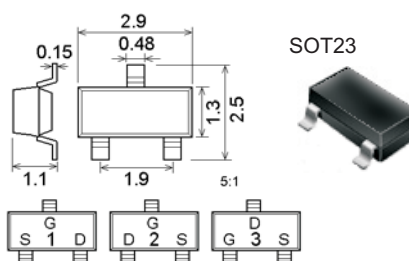
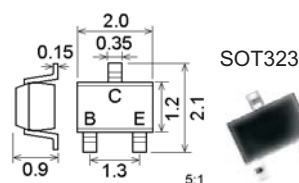
- P (W)** - nejvyšší dovolená výkonová ztráta na tranzistoru
- f (MHz)** - nejvyšší pracovní kmitočet tranzistoru
- U<sub>ds</sub> (V)** - nejvyšší dovolené stejnosm. napětí Drain - Source
- I<sub>d</sub> (A)** - nejvyšší dovolený proud elektrodou Drain
- R<sub>ds</sub> (Ω)** - odpor Drain - Source v sepnutém stavu
- t on/off (ns)** - čas sepnutí / vypnutí; (ONdelay+rise / OFFdelay+fall)

# TRANZISTORY BIPOLÁRNÍ SMD

## Tranzistory nf SMD

objednáací název		Uce	Ic	P	B	f	Uces	pouzdro
NPN	PNP	V	A	W		MHz	V	
■ BC848W	■ BC858W	30	0.1	0.2	110~800	100	0.2	SOT323
■ BC846W		65	0.1	0.2	110~450	100	0.2	SOT323
■ BC846BW	■ BC856BW	65	0.1	0.2	200~450	100	0.2	SOT323
■ BC847A	■ BC857A	45	0.1	0.25	110~220	100	0.3	SOT23
■ BC847C	■ BC857C	45	0.1	0.25	420~800	100	0.3	SOT23
■ BC847B	■ BC857B	45	0.1	0.25	200~450	100	0.2	SOT23
■ BC850C	# BC860C	45	0.1	0.25	420~800	100	0.2	SOT23
■ PMBT3904	■ PMBT3906	40	0.2	0.25	30~300	300	0.3	SOT23
■ MMBTA42	■ MMBTA92	300	0.5	0.3	> 25	50	0.5	SOT23
■ BC817-25	■ BC807- 25	45	0.5	0.31	160~400	80	0.7	SOT23
■ BC817-40	■ BC807- 40	45	0.5	0.31	250~600	80	0.7	SOT23
■ BC846B	■ BC856B	65	0.1	0.31	200~450	150	0.3	SOT23
■ FMMT458TA		400	0.23	0.5	100~300	50	0.5	SOT23
	■ FMMT560TA	500	0.15	0.5	80~300	60	0.5	SOT23
■ BCX54-16	■ BCX51-16	45	1.5	1.0	100~250	100	0.5	SOT89
■ BCX55-16	■ BCX52-16	60	1.5	1.0	100~250	100	0.5	SOT89
■ BCX56-16	■ BCX53-16	80	1.5	1.0	100~250	100	0.5	SOT89
■ BCP55-16	■ BCP52-16	60	1.0	1.3	100~250	115	0.5	SOT223
	■ BCP56-16	80	1.0	1.5	100~250	130	0.5	SOT223
	■ BCP53-16	80	1.5	1.5	100~250	50	0.5	SOT223
■ BDP949		60	3.0	5.0	> 50	100	0.5	SOT223

novinka!



## Tranzistory Darlington SMD

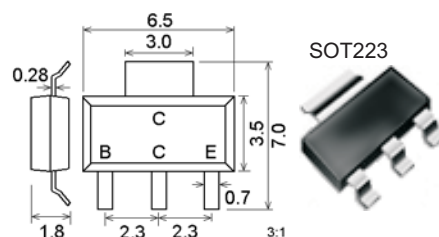
objednáací název	Uce	Ic	P	B	f	Uces	pouzdro
NPN	V	mA	W		MHz	V	
■ BCV47	60	0.5	0.25	> 10 000	170	1.0	SOT23

novinka!

## Tranzistory s vestavěnými rezistory (BRT) SMD

objednáací název	Uce	Ic	P	B	f	Uces	R1	R2	pouzdro
NPN	V	mA	W		MHz	V	kΩ	kΩ	
■ BCR512	50	500	0.33	>60	100	0.3	4.7	4.7	SOT23

novinka!



## Dvojice tranzistorů nf SMD

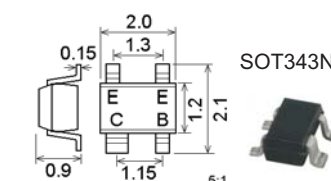
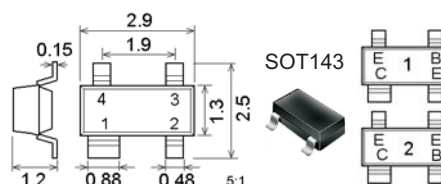
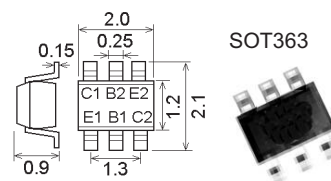
objednáací název	Uce	Ic	P	B	f	Uces	pouzdro
NPN	V	mA	W		MHz	V	
■ BC846S	65	100	0.2	>110	100	0.3	SOT363

novinka!

## Tranzistory vf > 1GHz SMD

objednáací název	Uce	Ic	P	G	f	pouzdro
NPN	V	mA	W	dB	GHz	
■ BFS17P	15	25	0.3	10	2.5	SOT23
■ BFR92A	15	25	0.3	14	5	SOT23
■ BFR93A	12	35	0.3	13	6	SOT23
■ AT41511T	12	50	0.2	15.5	8	SOT143(1)
■ BFG67	10	50	0.3	17	8	SOT143(2)
■ BFG540W	15	120	0.5	10	9	SOT343N

novinka!



### Bipolární Tranzistory - parametry

**Uce (V)** - nejvyšší dovolené napětí kolektor - emitor

**Uces(V)** - saturační napětí kolektor-emitor

**Ic (A)** - nejvyšší dovolený proud kolektoru

**P (W)** - nejvyšší dovolená výkonová ztráta

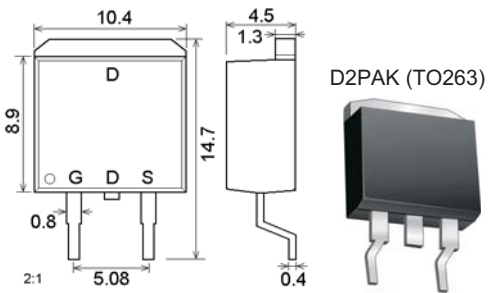
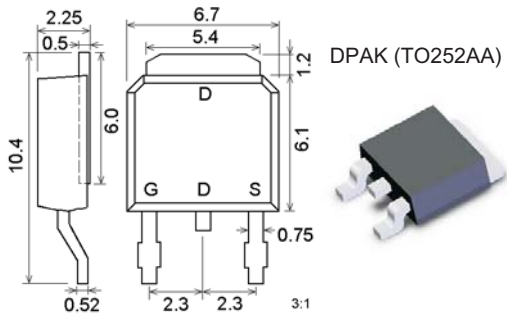
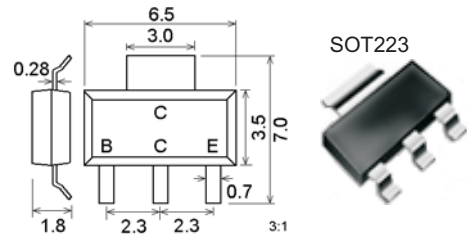
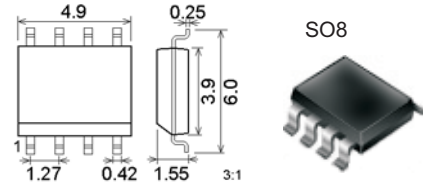
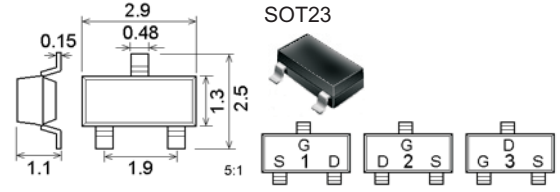
**B** - stejnosměrný zesilovací činitel

**G (dB)** - zisk

**f (MHz)** - nejvyšší pracovní kmitočet

## Tranzistory MOSFET SMD

objednáací název	kanál	U <sub>ds</sub>	I <sub>d</sub>	P	g <sub>fs</sub>	ton/off	R <sub>ds(on)</sub>	pouzdro
kanál N	V	A	W	S	ns	mΩ		
FDV302P	P	25	0.12	0.35	0.14	13 / 14	10000	SOT23 (3)
BSS84	P	50	0.13	0.25	0.05	4 / 24	5000	SOT23 (3)
BSS83P	P	60	0.33	0.36	0.47	94 / 117	2000	SOT23 (3)
FDV304P	P	25	0.46	0.35	0.8	15 / 90	1100	SOT23 (3)
IRLML6302	P	20	0.78	0.54	0.56	30 / 45	600	SOT23 (3)
BSS215P	P	20	1.5	0.5	4.5	16 / 29	150	SOT23 (3)
TSM2301CX	P	20	2.8	0.9	6.5	24 / 160	130	SOT23 (3)
AO3413	P	20	3	1.4	12	43 / 109	80	SOT23 (3)
IRLML5203	P	30	3	1.25	3.1	30 / 140	98	SOT23 (3)
IRLML6402	P	20	3.7	1.3	6	400 / 970	56	SOT23 (3)
AO3401A	P	30	4	1.4	17	10 / 50	50	SOT23 (3)
IRLML6401	P	12	4.3	1.3	86	43 / 460	50	SOT23 (3)
IRLTS2242	P	20	6.9	2	8.5	24 / 150	32	SOT23-6
IRF7404	P	20	7.7	2.5	6.8	46 / 165	40	SO8
IRF7416	P	30	10	2.5	5.6	70 / 120	20	SO8
AO4437	P	12	11	3	38	58 / 253	16	SO8
IRF7220	P	14	11	2.5	8.4	440 / 1200	12	SO8
IRF7425	P	20	15	2.5	44	33 / 390	8.2	SO8
IRFR9310	P	400	1.8	50	0.91	21 / 50	7000	DPAK
IRFR9120N	P	100	6.6	40	1.4	60 / 60	480	DPAK
IRFR9024N	P	55	11	38	2.5	70 / 60	175	DPAK
IRFR5410	P	100	13	66	3.2	75 / 90	205	DPAK
IRFR5505	P	55	18	57	4.2	40 / 35	110	DPAK
IRFR5305	P	55	31	110	8	80 / 100	65	DPAK
IRF9224S	P	60	11	60	1.4	80 / 45	280	D2PAK
IRF9530NS	P	100	14	79	3.2	75 / 90	200	D2PAK
IRF9540NS	P	100	23	140	5.3	80 / 100	117	D2PAK
IRF4905S	P	55	74	200	21	115 / 155	20	D2PAK
2N7002	N	60	0.12	0.2	0.32	20 / 40	4300	SOT23 (3)
BSS123	N	100	0.15	0.25	0.40	15 / 30	3200	SOT23 (3)
BSN20	N	50	0.17	0.83	0.17	8 / 16	2800	SOT23 (3)
BSS138	N	50	0.22	0.36	0.45	20 / 40	1800	SOT23 (3)
FDV301N	N	25	0.22	0.35	0.2	9 / 7	5000	SOT23 (3)
FDV303N	N	25	0.68	0.35	1.5	12 / 30	450	SOT23 (3)
IRLML2402	N	20	1.2	0.54	1.3	12 / 15	250	SOT23 (3)
IRLML2030	N	30	2.7	1.3	2.6	8 / 8	100	SOT23 (3)
IRLML0060	N	60	2.7	1.25	7.6	12 / 11	116	SOT23 (3)
AO3406	N	30	3.6	1.4	11	6 / 34	50	SOT23 (3)
IRLML6246	N	20	4.1	1.3	10	9 / 17	46	SOT23 (3)
IRLML2502	N	20	4.2	1.25	5.8	18 / 80	45	SOT23 (3)
TSM2312CX	N	20	4.9	0.75	40	55 / 80	33	SOT23 (3)
IRLML0030	N	30	5.3	1.3	9.5	10 / 12	27	SOT23 (3)
AO3400A	N	30	5.7	1.4	33	6 / 29	26.5	SOT23 (3)
IRFML8244	N	25	5.8	1.25	10	5 / 12	24	SOT23 (3)
IRLML6244	N	20	6.3	1.3	17	13 / 31	21	SOT23 (3)
IRF7468	N	40	9.4	2.5	27	10 / 24	0.015	SO8
IRF7413	N	30	13	2.5	10	60 / 100	0.011	SO8
IRF8734	N	30	21	2.5	85	29 / 23	0.0035	SO8
BSP296	N	100	1.1	1.8	1.2	13 / 59	0.7	SOT223
IRLL024N	N	55	3.1	1	3.3	29 / 43	65	SOT223
IRFL024Z	N	55	5.1	1.0	6.2	30 / 50	58	SOT223
BSP149	N	200	0.66	1.8	0.4	9 / 65	3500	SOT223
IRFR310	N	400	1.7	25	0.9	18 / 32	3600	DPAK
IRFRC20	N	600	2	42	1.4	33 / 55	4400	DPAK
IRFR220N	N	200	5	43	2.6	20 / 30	600	DPAK
IRLR120N	N	100	10	48	3.1	40 / 45	185	DPAK
IRLR024N	N	55	17	45	8.3	80 / 50	65	DPAK
IRLR2705	N	55	28	68	11	110 / 50	40	DPAK
IRFR3806	N	60	43	71	41	45 / 95	15.8	DPAK
IRL640S	N	200	17	125	16	90 / 95	180	D2PAK
IRF540NS	N	100	33	130	21	46 / 75	44	D2PAK
IRL540NS	N	100	36	140	14	90 / 101	44	D2PAK
IRF2804S	N	40	75	300	130	135 / 260	2	D2PAK
IRL1404ZS	N	40	75	230	120	200 / 80	3.1	D2PAK
IRF3205S	N	55	110	200	44	115 / 115	8	D2PAK
IRL2203NS	N	30	116	180	73	171 / 89	7	D2PAK
MCP87055T-U/LC	N	25	60	1.8	92	15 / 14	7	DFN8 (3x3)
MCP87022T-U/MF	N	25	100	2.2	155	35 / 38	2.6	DFN8 (5x6)
MCP87050T-U/MF	N	25	100	2.2	101	23 / 16	6	DFN8 (5x6)



### FET tranzistory SMD - parametry

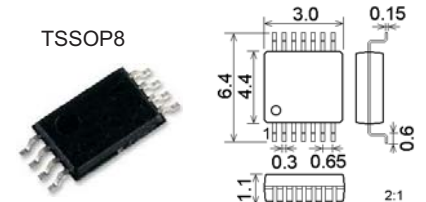
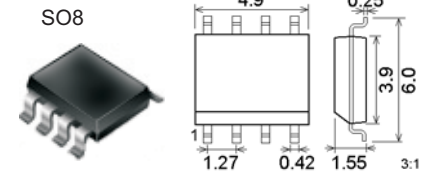
- P (W)** - nejvyšší dovolená výkonová ztráta na tranzistoru
- f (MHz)** - nejvyšší pracovní kmitočet tranzistoru
- U<sub>ds</sub> (V)** - nejvyšší dovolené stejnosměrné napětí Drain - Source
- I<sub>ds</sub> (mA)** - proud elektrodou Drain pro U<sub>gs</sub>=0
- I<sub>d</sub> (mA)** - nejvyšší dovolený proud elektrodou Drain
- R<sub>ds</sub> (Ω)** - odpor Drain - Source v sepnutém stavu
- g<sub>fs</sub> (mS)** - strmost (vstupní admitance)
- t<sub>on/off</sub> (ns)** - čas sepnutí / vypnutí; (ONdelay+rise / OFFdelay+fall)



# TRANZISTORY FET, IGBT

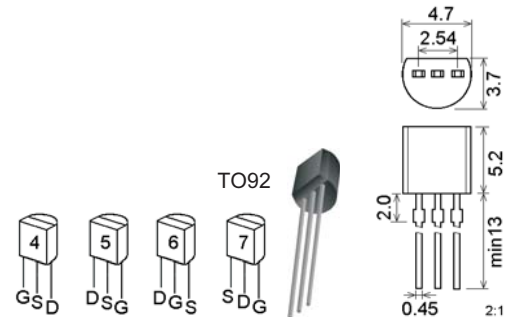
## Dvojice tranzistorů MOSFET SMD

objednávací název	kanál	Uds V	Id A	P W	gfs S	ton/off ns	Rdson mΩ	pouzdro
■ IRF7103	2x N	50	3	2	3.8	17 / 70	130	SO8
■ IRF7341	2x N	55	4.7	2	7.9	13 / 45	50	SO8
■ IRF7311	2x N	20	6.6	2	20	25 / 69	29	SO8
■ IRF7331	2x N	20	7	2	14	30 / 160	30	SO8
■ IRL6372	2x N	30	8.1	2	30	19 / 49	17.9	SO8
■ IRF8313	2x N	30	9.7	2	23	18 / 13	15.5	SO8
■ IRF7342	2x P	55	3.4	2	3.3	24 / 65	105	SO8
■ IRF7304	2x P	20	4.7	2	4	35 / 84	90	SO8
■ IRF7316	2x P	30	4.9	2	7.7	26 / 66	58	SO8
■ AO4821	2x P	12	9	2	45	820 / 11	19	SO8
■ AO8807L	2x P	12	6.5	1.4	45	820 / 11	20	TSSOP8
■ IRF7343	N	55	4.7	2	7.9	12 / 45	50	SO8
	P	55	3.4		3.3	14 / 65	105	
■ IRF7307	N	20	5.2	2	8.3	51 / 83	50	SO8
	P	20	4.3		4	35 / 83	90	
■ IRF7319	N	30	6.5	2	14	17 / 43	29	SO8
	P	30	4.9		7.7	26 / 66	58	
■ IRF7389	N	30	7.3	2.5	14	17 / 43	29	SO8
	P	30	5.3		7.7	26 / 66	58	



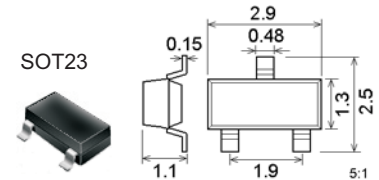
## Tranzistory J-FET

objednávací název	Udg V	Id mA	P W	g fs mS	Rds Ω	pouzdro
■ J112	35	5	0.35		50	TO92 (5)
■ BFR245A	30	2~6.5	0.35	3~6.5		TO92 (4)
■ BFR245B	30	6~13	0.35	>4.5		TO92 (4)
■ BFR245C	30	6~15	0.35	3~6.5		TO92 (4)
■ BFR245D	30	12~25	0.35	3~6.5		TO92 (4)



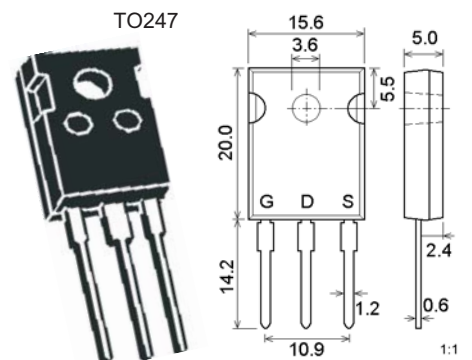
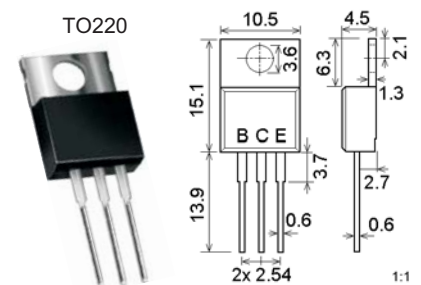
## Tranzistory J-FET SMD

objednávací název	Udg V	Id mA	P W	g fs mS	Rds Ω	pouzdro
■ BFR31	30	1~5	0.25	1~4.5		SOT23
■ BF545A	30	2~6.5	0.25	3~6.5		SOT23
■ MMBFJ177	25	1.5~20	0.225		300	SOT23



## Tranzistory IGBT

objednávací název	Uce V	Ic A	P W	anti-paralelní vnitřní dioda	Uce(on) V	@Vge V	@Ic A	pouzdro
■ IRG4BC20UD	600	13	60	ANO	1.85	15	6.5	TO220
■ IRG4BC20U	600	13	60	NE	1.85	15	6.5	TO220
■ IRG4BC20KD	600	16	60	ANO	2.27	15	9	TO220
■ IRG4BC20FD	600	16	60	ANO	1.66	15	9	TO220
■ IRG4BC20S	600	19	60	NE	1.4	15	10	TO220
■ IRG4BC30UD	600	23	100	ANO	1.95	15	12	TO220
■ IRG4BC30U	600	23	100	NE	1.95	15	12	TO220
■ IRG4BC30K	600	28	100	NE	2.21	15	16	TO220
■ IRG4BC40U	600	40	160	NE	1.72	15	20	TO220
■ IRGB30B60K	600	78	370	NE	1.95	15	30	TO220
■ IRG4PH40UD	1200	41	160	ANO	2.43	15	21	TO247
■ IRG4PH40U	1200	41	160	NE	2.43	15	21	TO247
■ IRG4PC40FD	600	49	160	ANO	1.50	15	27	TO247
■ IRG4PF50W	900	51	200	NE	2.25	15	28	TO247
■ IRG4PC50W	600	55	200	NE	2.30	15	27	TO247



### IGBT Tranzistory - parametry

**Uce (V)** - nejvyšší dovolené napětí kolektor - emitor

**Uce(on) (V)** - úbytek napětí kolektor-emitor při definovaném Vge a Ic

**Uge (V)** - hodnota napětí gate - emitor při kterém je změřeno Uce(on)

**Ic (A)** - nejvyšší dovolený proud kolektoru

**@Ic (A)** - hodnota proudu kolektoru při kterém je změřeno Uce(on)

**P (W)** - nejvyšší dovolená výkonová ztráta

■ součástka se doplňuje na sklad

# součástka na skladě, výprodeje

Dodací podmínky neoznačených součástek sdělíme na požádání